

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1
 Stylesheet Version v1.2

EPAS ID: PAT3459445

SUBMISSION TYPE:	NEW ASSIGNMENT	
NATURE OF CONVEYANCE:	ASSIGNMENT	
CONVEYING PARTY DATA		
	Name	Execution Date
	SIXPOINT MATERIALS, INC.	09/17/2013
RECEIVING PARTY DATA		
Name:	SEOUL SEMICONDUCTOR CO., LTD.	
Street Address:	148-29, KASAN-DONG, KEUMCHUN-GU	
City:	SEOUL	
State/Country:	KOREA, REPUBLIC OF	
PROPERTY NUMBERS Total: 1		
	Property Type	Number
	Application Number:	14811799
CORRESPONDENCE DATA		
Fax Number:		
<i>Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.</i>		
Phone:	6504348410	
Email:	USPTO_mail@siiplaw.com	
Correspondent Name:	STRATEGIC INNOVATION IP LAW OFFICES, P.C	
Address Line 1:	1250 OAKMEAD PARKWAY, SUITE 210	
Address Line 4:	SUNNYVALE, CALIFORNIA 94085	
ATTORNEY DOCKET NUMBER:	SIXPOI-012USDIV1	
NAME OF SUBMITTER:	CHARLES D. HOLLAND	
SIGNATURE:	/ Charles D. Holland /	
DATE SIGNED:	07/28/2015	
Total Attachments: 4		
source=SIXPOI_012USDIV1_Assign#page1.tif		
source=SIXPOI_012USDIV1_Assign#page2.tif		
source=SIXPOI_012USDIV1_Assign#page3.tif		
source=SIXPOI_012USDIV1_Assign#page4.tif		

ASSIGNMENT

This Assignment by SixPoint Materials, Inc., a corporation organized and existing under the laws of Delaware and having a usual place of business at 37 Industrial Way, 106, Buellton, CA 93427 (hereinafter referred to as the assignor), witnesseth:

WHEREAS, said assignor owns the entire right, title, and interest in the invention(s) as set forth in Appendix A by virtue of assignments recorded at the noted reel and frame numbers;

WHEREAS, Seoul Semiconductor Co., Ltd. (hereinafter "ASSIGNEE"), a corporation organized and existing under the laws of the Republic of Korea, and having a usual place of business at 148-29, Kusan-Dong, Keumchun-Gu, Seoul, Korea, desires to acquire an interest therein, in accordance with agreements duly entered into with us/me;

NOW, THEREFORE, to all whom it may concern, be it known that, for and in consideration of said agreements and of other good and valuable consideration, the receipt of which is hereby acknowledged, we/I have sold, assigned and transferred and by these presents do hereby sell, assign and transfer unto said ASSIGNEE, a fifty percent (50%) undivided interest, in and throughout the United States of America, its territories and all foreign countries, in and to the invention(s) described in said applications, together with a fifty percent (50%) undivided interest in and to said applications and such Patents as may issue thereon or claim priority under United States law or international convention, including but not limited to non-provisionals, continuations, continuations-in-part, divisionals, reissues, reexaminations, extensions, and substitutions of said application or such Patents; said invention(s), applications and Patents to be held and enjoyed by said ASSIGNEE for its own use and behalf and for such of ASSIGNEE's Affiliates as are permitted under the "IP Agreement" dated November 23, 2012, to the full end of the term for which said Patents may be granted, provided that if ASSIGNEE before November 23, 2017 fails to pay any costs for a filing related to the invention(s) described in any of said applications, ASSIGNEE by its signature below hereby assigns all of its rights, title, and interest in and to the invention(s) and said applications for which said costs were not paid to assignor or assignor's successors in interest;

AND, we/I hereby further agree for ourselves/myself and our/my executors and administrators to execute upon request any other lawful documents and likewise to perform any other lawful acts which may be deemed necessary to secure fully the interest in the aforesaid invention(s) to said ASSIGNEE, but at its or their expense and charges, including the execution of non-provisional, substitution, continuation, continuation-in-part, divisional, reissue, reexamination, or corresponding foreign or international patent applications;

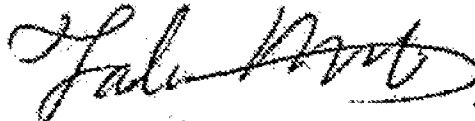
AND, we/I hereby further agree to provide statements or testimony in any interference or other proceeding in which said invention(s) or any application or patent directed thereto may be involved;

AND, subject to the terms herein, we/I hereby authorize and request the Director of the United States Patent and Trademark Office and the empowered officials of all other governments to issue such Patent as shall be granted upon said applications, or applications based thereon, to include said ASSIGNEE as a joint owner.

IN TESTIMONY WHEREOF, we/I have hereunto set our/my signatures on the date(s) set forth below.

9/17/2013

Date

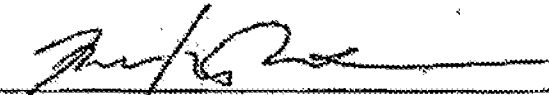


By Tadao Hashimoto, CEO
SixPoint Materials, Inc.
37 Industrial Way, 106
Buellton, CA 93427
U.S.A.

Assignee hereby accepts the assignment of an interest in the invention(s) and the above-identified applications and/or patents.

9/17/2013

Date



By Kibum Nam, CTO
Seoul Semiconductor Co., Ltd.
148-29, Kasan-Dong, Keumchun-Gu,
Seoul, Korea

#78629

**ASSIGNMENT SIXPOINT MATERIALS, INC. TO SEOUL SEMICONDUCTOR CO., LTD.
APPENDIX A**

Attorney Docket No.	Application No.	Title	Filed Date	Inventor(s)	Inventor Assignment Reel/Frame No.
SIXPOL-012US	13/781,509	COMPOSITE SUBSTRATE OF GALLIUM NITRIDE AND METAL OXIDE	02/28/2013	Tadao Hashimoto	030222/0860
SIXPOL-012WO	PCT/US2013/028427	COMPOSITE SUBSTRATE OF GALLIUM NITRIDE AND METAL OXIDE	02/28/2013	Tadao Hashimoto	030660/0544
SIXPOL-013US	13/781,543	BISMUTH-DOPED SEMI-INSULATING GROUP III NITRIDE WAFER AND ITS PRODUCTION METHOD	02/28/2013	Tadao Hashimoto	030223/0352
				Edward Letts	030223/0352
				Sierra Hoff	030223/0352
SIXPOL-013WO	PCT/US2013/028416	BISMUTH-DOPED SEMI-INSULATING GROUP III NITRIDE WAFER AND ITS PRODUCTION METHOD	02/28/2013	Tadao Hashimoto	030689/0980
				Edward Letts	030689/0826
				Sierra Hoff	030854/0165
SIXPOL-014US1	13/833,443	METHOD OF GROWING GROUP III NITRIDE CRYSTALS	03/15/2013	Tadao Hashimoto	030689/0685
				Edward Letts	030689/0564
				Sierra Hoff	030854/0856
SIXPOL-014US2	13/834,015	METHOD OF GROWING GROUP III NITRIDE CRYSTALS	03/15/2013	Tadao Hashimoto	030689/0355
				Edward Letts	030689/0484
				Sierra Hoff	030854/0416
SIXPOL-014WO	PCT/US2013/032103	METHOD OF GROWING GROUP III NITRIDE CRYSTALS	03/15/2013	Tadao Hashimoto	030688/0920
				Edward Letts	030689/0031
				Sierra Hoff	030855/0033

ASSIGNMENT SIXPOINT MATERIALS, INC. TO SEOUL SEMICONDUCTOR CO., LTD.

APPENDIX A

Attorney Docket No.	Application No.	Title	Filed Date	Inventor(s)	Inventor Assignment Recd/Frame No.
SIXPOL-015US1	13/834,871	GROUP III NITRIDE WAFER AND ITS PRODUCTION METHOD	03/15/2013	Tadao Hashimoto	030688/0408
				Edward Letts	030688/0657
				Sierra Hoff	030855/0293
SIXPOL-015US2	13/835,636	GROUP III NITRIDE WAFER AND ITS PRODUCTION METHOD	03/15/2013	Tadao Hashimoto	030688/0143
				Edward Letts	030688/0247
				Sierra Hoff	030855/0457
SIXPOL-015WO	PCT/US2013/032006	GROUP III NITRIDE WAFER AND ITS PRODUCTION METHOD	03/15/2013	Tadao Hashimoto	030687/0945
				Edward Letts	030688/0019
				Sierra Hoff	030855/0617
SIXPOL-016US	13/798,530	GROUP III NITRIDE WAFERS AND FABRICATION METHOD AND TESTING METHOD	03/13/2013	Tadao Hashimoto	030661/0155
SIXPOL-016WO	PCT/US2013/030913	GROUP III NITRIDE WAFERS AND FABRICATION METHOD AND TESTING METHOD	03/13/2013	Tadao Hashimoto	030660/0756

PL-83885